

**AMENDMENTS TO THE SPECIFICATION**

**Page 32, please replace paragraph no. 2, with the following amended paragraph:**

Both of upper and lower surfaces of each sample were subjected to nickel plating. Each sample was fitted to a package for a semiconductor module having a sectional structure illustrated in a schematic view of Fig. 8. Then, a thermal cycle test was carrier out. In Fig. 8, the reference numeral 21 represents an intermediate substrate made of the above-mentioned composite material of the present invention, the reference numeral 22 represents a silicon semiconductor device having a thermal expansion coefficient of about  $4 \times 10^{-6}/^{\circ}\text{C}$ , the reference numeral 23 represents an upper substrate made of aluminum nitride (AlN) based ceramics having a thermal expansion coefficient of about  $4 \times 10^{-6}/^{\circ}\text{C}$ , and the reference numeral 24 represents a base substrate made of copper having a thermal expansion coefficient of  $17 \times 10^{-6}/^{\circ}\text{C}$ . An envelope member 25 made of ceramics, a metal, or the like is connected onto the intermediate substrate 21 of the present invention via silver solder 26. The intermediate substrate 21 is connected to the base substrate 24 via silver-tin based solder 27 and further soldered to the envelope or peripheral member 25 by silver solder 26.